- Designed for Complementary Use with the TIP35 Series
- 125 W at 25°C Case Temperature
- 25 A Continuous Collector Current
- 40 A Peak Collector Current
- Customer-Specified Selections Available

SOT-93 PACKAGE (TOP VIEW) B 1 C 2 3

Pin 2 is in electrical contact with the mounting base.

MDTRAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	TIP36		-80		
Collector-base voltage (I _E = 0)	TIP36A	\ \ <u>\</u>	-100	V	
	TIP36B	V _{CBO}	-120	v	
	TIP36C		-140		
	TIP36		-40		
Collector-emitter voltage (I _B = 0)	TIP36A	V	-60	v	
	TIP36B	V _{CEO}	-80	V	
	TIP36C		-100		
Emitter-base voltage			-5	V	
Continuous collector current			-25	Α	
Peak collector current (see Note 1)			-40	Α	
Continuous base current			-5	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			125	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			3.5	W	
Unclamped inductive load energy (see Note 4)			90	mJ	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range			-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds			250	°C	

NOTES: 1. This value applies for $t_p \le 0.3$ ms, duty cycle $\le 10\%$.

- 2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -0.4 A, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.



TIP36, TIP36A, TIP36B, TIP36C PNP SILICON POWER TRANSISTORS

JULY 1968 - REVISED MARCH 1997

electrical characteristics at 25°C case temperature

PARAMETER			TEST CONDITION	ONS	MIN TYP MAX			UNIT	
V _{(BR)CEO}	Collector-emitter breakdown voltage	$I_C = -30 \text{ mA}$ $I_B = 0$ (see Note 5)		TIP36	-40				
			I _B = 0	TIP36A	-60			V	
				TIP36B	-80				
				TIP36C	-100				
		V _{CE} = -80 V	$V_{BE} = 0$	TIP36			-0.7		
1	Collector-emitter	$V_{CE} = -100 \text{ V}$	$V_{BE} = 0$	TIP36A			-0.7	mA	
ICES	cut-off current	$V_{CE} = -120 \text{ V}$	$V_{BE} = 0$	TIP36B			-0.7	ША	
		$V_{CE} = -140 \text{ V}$	$V_{BE} = 0$	TIP36C			-0.7		
	Collector cut-off	V _{CE} = -30 V	I _B = 0	TIP36/36A			-1	mA	
ICEO	current	V _{CE} = -60 V	$I_B = 0$	TIP36B/36C			-1	ША	
1	Emitter cut-off	V _{EB} = -5 V	I _C = 0				-1	mA	
I _{EBO}	current						-,	ША	
h	Forward current	V _{CE} = -4 V	I _C = -1.5 A	(see Notes 5 and 6)	25				
h _{FE}	transfer ratio	V _{CE} = -4 V	$I_{C} = -15 \text{ A}$		10		50		
V	Collector-emitter	I _B = -1.5 A	I _C = -15 A	(see Notes 5 and 6)			-1.8	V	
V _{CE(sat)}	saturation voltage	I _B = -5 A	$I_{C} = -25 \text{ A}$				-4	V	
V _{BE}	Base-emitter	V _{CE} = -4 V	I _C = -15 A	(see Notes 5 and 6)			-2	V	
V BE	voltage	V _{CE} = -4 V	$I_{C} = -25 \text{ A}$				-4	V	
h.	Small signal forward	V - 10 V	V _{CE} = -10 V I _C = -1 A	I _C = -1 A	f = 1 kHz	25			
h _{fe}	current transfer ratio	ACE - 310 A	IC = -I M I = I KHZ	I – I NIIZ	25				
h _{fe}	Small signal forward	V _{CE} = -10 V	I _C = -1 A f = 1 MH	f _ 1 M⊔→	3				
l' lfel	current transfer ratio	ACE - 110 A		I — I IVII IZ	3				

NOTES: 5. These parameters must be measured using pulse techniques, t_p = 300 μs , duty cycle \leq 2%.

thermal characteristics

PARAMETER			TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = -15 A	$I_{B(on)} = -1.5 A$	$I_{B(off)} = 1.5 A$		1.1		μs
t _{off}	Turn-off time	$V_{BE(off)} = 4.15 \text{ V}$	$R_L = 2 \Omega$	$t_p = 20 \ \mu s, \ dc \le 2\%$		0.8		μs

 $^{^{\}dagger} \ \ \mbox{Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.}$

PRODUCT INFORMATION

^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN vs COLLECTOR CURRENT $\frac{1000}{T_{C}} = -4 \text{ V}$ $\frac{1000}{T_{C}} = 25 \,^{\circ}\text{C}$ $\frac{1}{T_{D}} = 300 \, \mu\text{s}$, duty cycle < 2% $\frac{1}{T_{C}} = 25 \,^{\circ}\text{C}$ $\frac{1}{T_{C$

Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE

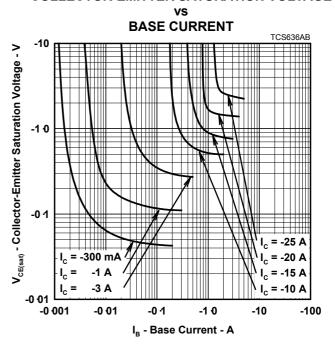


Figure 2.

BASE-EMITTER VOLTAGE

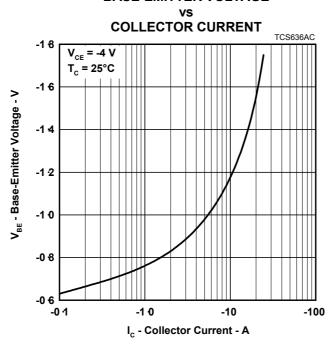
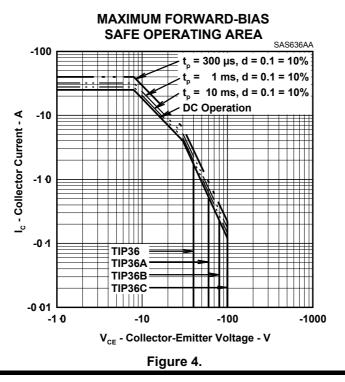


Figure 3.

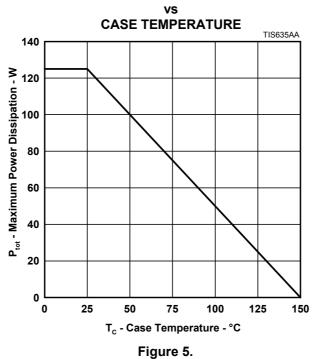


MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

MAXIMUM POWER DISSIPATION



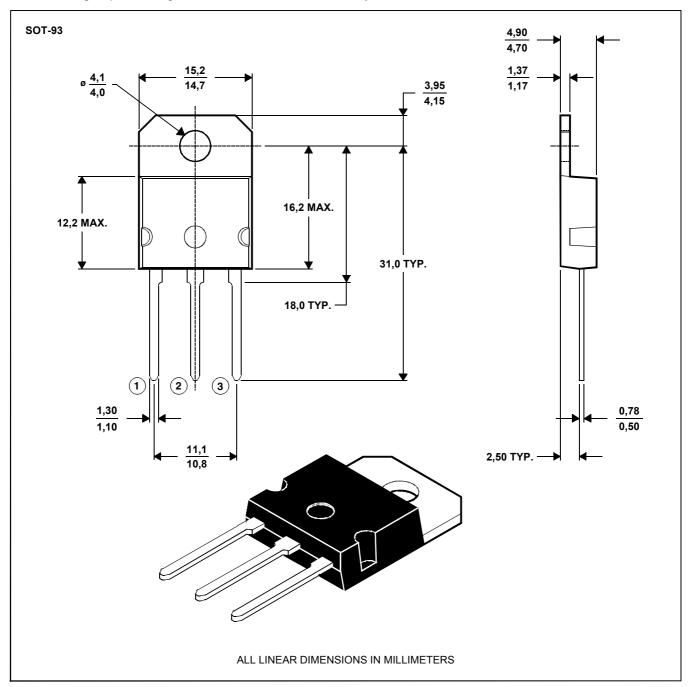
PRODUCT INFORMATION

MECHANICAL DATA

SOT-93

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: The centre pin is in electrical contact with the mounting tab.

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TIP36, TIP36A, TIP36B, TIP36C PNP SILICON POWER TRANSISTORS

JULY 1968 - REVISED MARCH 1997

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